

General Description

The Sanrise SRC65R024BS is a high voltage power MOSFET, fabricated using advanced super junction technology. The resulting device has extremely low on resistance, low gate charge and fast switching time, making it especially suitable for applications which require superior power density and outstanding efficiency.

The SRC65R024BS break down voltage is 650V and it has a high rugged avalanche characteristics. The SRC65R024BS is available in TO-247 package.

Features

- Ultra Low $R_{DS(ON)} = 24m\Omega @ V_{GS} = 10V$.
- Ultra Low Gate Charge, $Q_g = 408nC$ typ.
- $V_{ds}@T_{jmax} = 700v$.
- Intrinsic Fast-Recovery Body Diode
- Fast switching capability
- Robust design with better EAS performance
- Non-automotive Qualified
- Ultra-fast body diode

Application

- EV Charger
- Server / Telecom

Ordering Information

SRC65R024BS□□-□		
Circuit Type	_____	E: Lead Free
Package	_____	G: Green
T: TO-247		Blank: Tube
		TR: Tape & Reel

Symbol

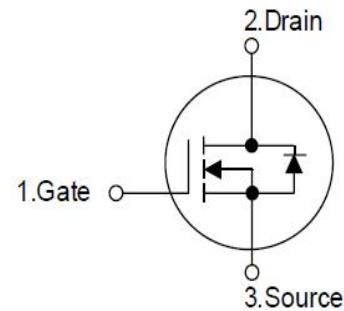


Figure 1 Symbol of SRC65R024BS

Package Type

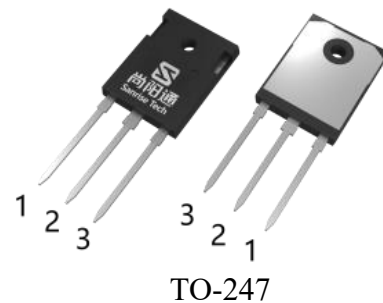


Figure 2 Package Type of SRC65R024BS

Package	Part Number	Marking ID	Packing Type
TO-247	SRC65R024BST-G	SRC65R024BSTG	Tube

Absolute Maximum Ratings^{Note 1}

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage (static)		V_{GSS}	±20	V
Gate-Source Voltage (dynamic), AC ($f > 1$ Hz)		V_{GSS}	±30	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	110	A
	$T_C = 100^\circ\text{C}$		69	
	$T_C = 125^\circ\text{C}$		49	
Power Dissipation ($T_C = 25^\circ\text{C}$, TO-247)		P_{tot}	595	W
Pulsed Drain Current (Note 2)		I_{DM}	330	A
Avalanche Energy, Single Pulse (Note 3)		E_{AS}	413	mJ
Avalanche Energy, Single Pulse (Note 4)		E_{AS}	6000	mJ
Avalanche Energy, Repetitive (Note 2)		E_{AR}	0.4	mJ
Avalanche Current, Repetitive (Note 2)		I_{AR}	3.5	A
Continuous Diode Forward Current		I_S	110	A
Diode Pulse Current		$I_{S,PULSE}$	330	A
MOSFET dv/dt Ruggedness, $V_{DS} \leq 480\text{V}$		dv/dt	80	V/ns
Reverse Diode dv/dt , $V_{DS} \leq 480\text{V}$, $I_{SD} \leq I_D$		dv/dt	50	V/ns
Operating Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 to 150	$^\circ\text{C}$
Lead Temperature (Soldering, 10 sec)		T_{LEAD}	260	$^\circ\text{C}$

Note:

1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. $I_{AS} = 3.5\text{A}$, $V_{DD} = 60\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$. Finish goods test condition.
4. $I_{AS} = 13.4\text{A}$, $V_{DD} = 60\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$. Typical Eas.

Thermal characteristics

Parameter (TO247-package)	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	-		0.21	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	-		62	

Electrical Characteristics

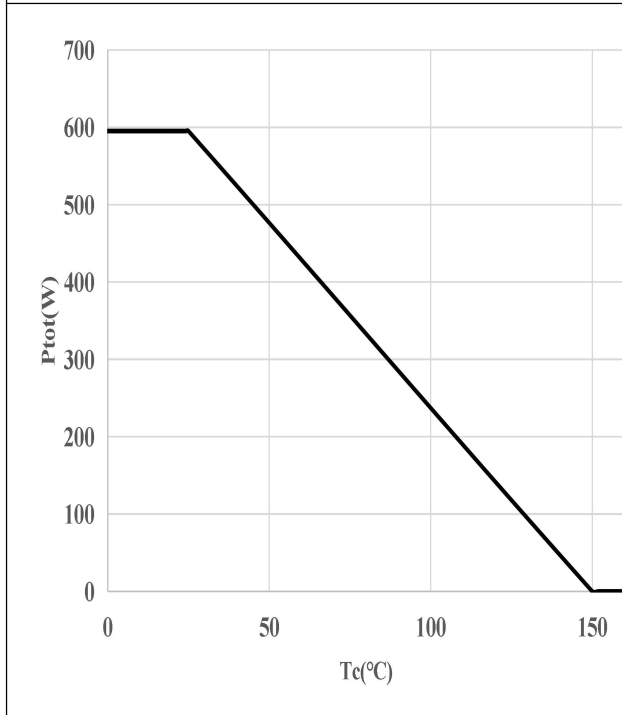
$T_J = 25^{\circ}\text{C}$, unless otherwise specified.

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250uA	650			V
Zero Gate Voltage Drain Current		I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	uA
Gate-Body Leakage Current	Forward	I _{GSSF}	V _{GS} =20V, V _{DS} =0V			200	nA
	Reverse	I _{GSSR}	V _{GS} =-20V, V _{DS} =0V			-200	
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =2.9mA	3.5	4.5	5.5	V
Static Drain-Source On-Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =40A		19	24	mΩ
Gate Resistance		R _G	f=1MHz, Open Drain		0.9		Ω
Dynamic Characteristics							
Input Capacitance		C _{ISS}	V _{DS} =400V, V _{GS} =0V, f=100kHz		8.3		nF
Output Capacitance		C _{OSS}			208		pF
Effective output capacitance, energy related ^{NOTE5}		C _{O(er)}	V _{GS} =0V, V _{DS} =0...400V		316		pF
Effective output capacitance, time related ^{NOTE6}		C _{O(tr)}			1722		
Turn-on Delay Time		t _{d(on)}	V _{DD} =400V, I _D =40A R _G =3.0Ω, V _{GS} =12V		87		ns
Rise Time		t _r			30		
Turn-off Delay Time		t _{d(off)}			205		
Fall Time		t _f			15		
Gate Charge Characteristics							
Gate to Source Charge		Q _{gs}	V _{DD} =400V, I _D =40A V _{GS} =0 to 10V		66		nC
Gate to Drain Charge		Q _{gd}			226		
Gate Charge Total		Q _g			408		
Gate Plateau Voltage		V _{plateau}			7.8		V
Reverse Diode Characteristics							
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} =0V, I _{SD} =40A		0.85	1.1	V
Reverse Recovery Time		t _{rr}	V _R =400V, I _F =40A dI _F /dt=100A/us		238		ns
Reverse Recovery Charge		Q _{rr}			3.2		uC
Peak Reverse Recovery Current		I _{rrm}			22		A

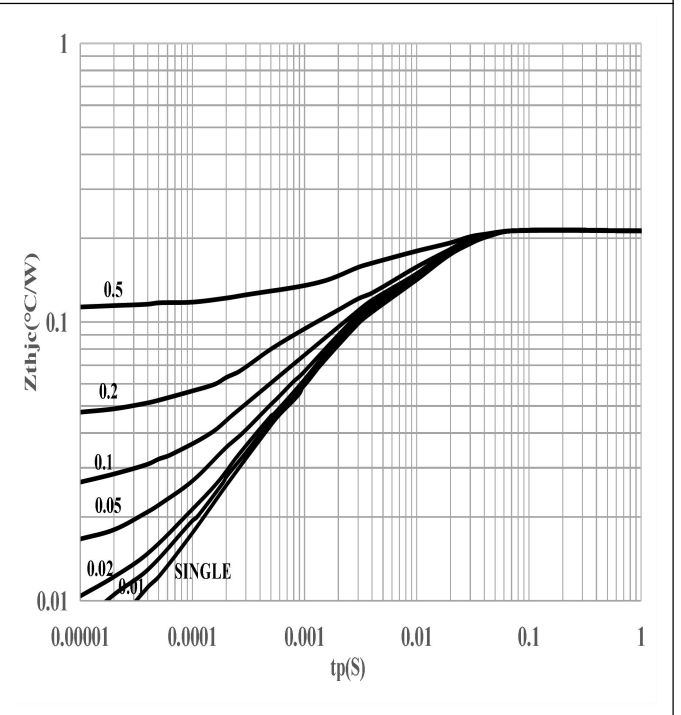
Note:

5. $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 400V

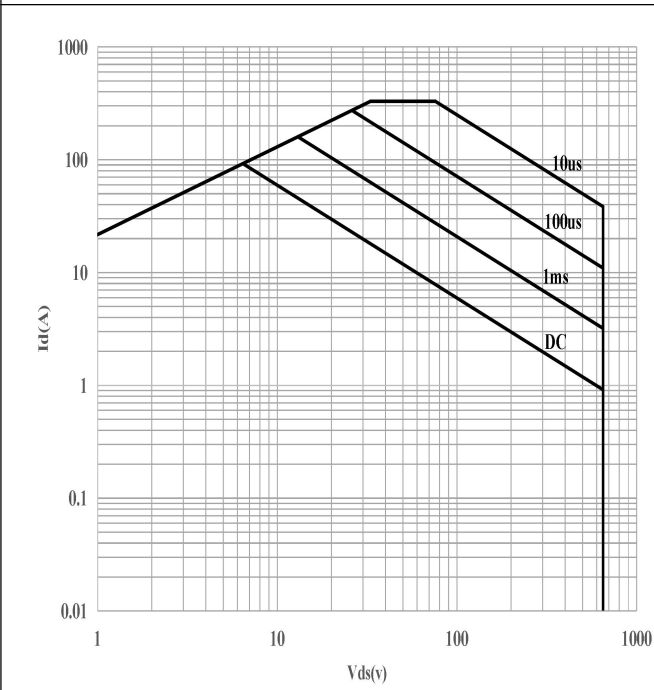
6. $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 400 V

Typical Performance Characteristics
Figure 3: Power Dissipation


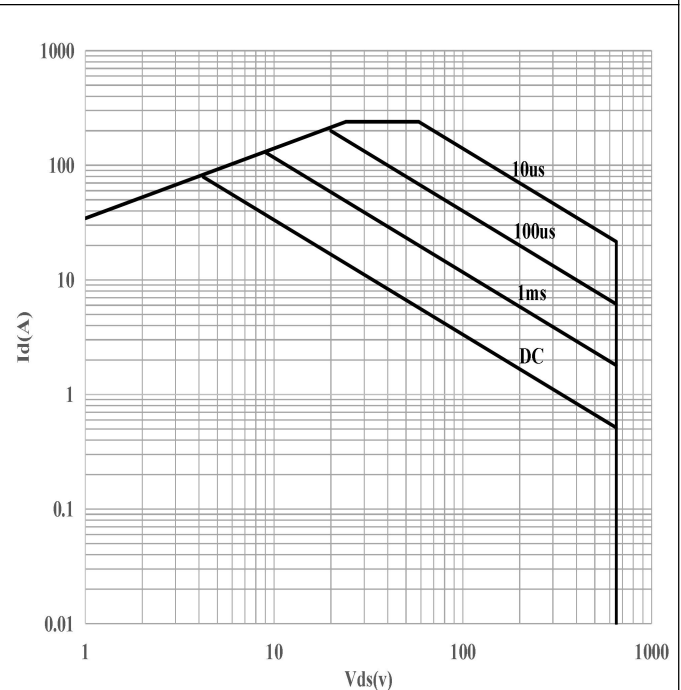
$$P_{\text{tot}} = f(T_c)$$

Figure 4: Max. Transient Thermal Impedance


$$Z_{(\text{thJC})} = f(t_p); \text{ parameter: } D = t_p/T$$

Figure 5: Safe Operating Area


$$I_{\text{D}} = f(V_{\text{DS}}); T_c = 25^{\circ}\text{C}; V_{\text{GS}} > 7\text{V}; \text{ parameter } t_p$$

Figure 6: Safe Operating Area


$$I_{\text{D}} = f(V_{\text{DS}}); T_c = 80^{\circ}\text{C}; V_{\text{GS}} > 7\text{V}; \text{ parameter } t_p$$

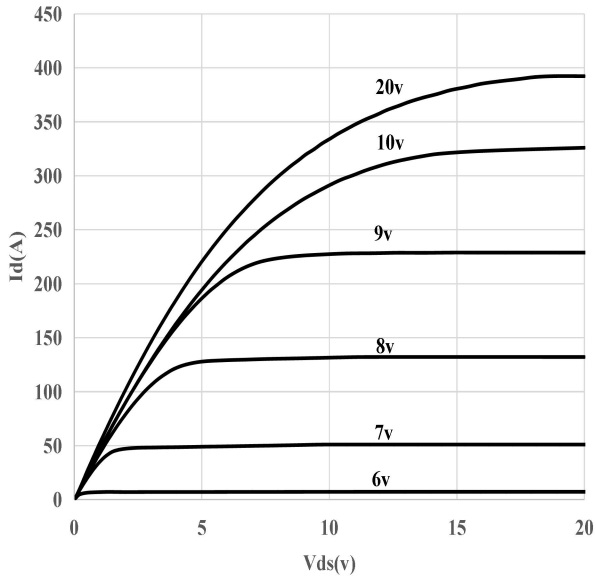
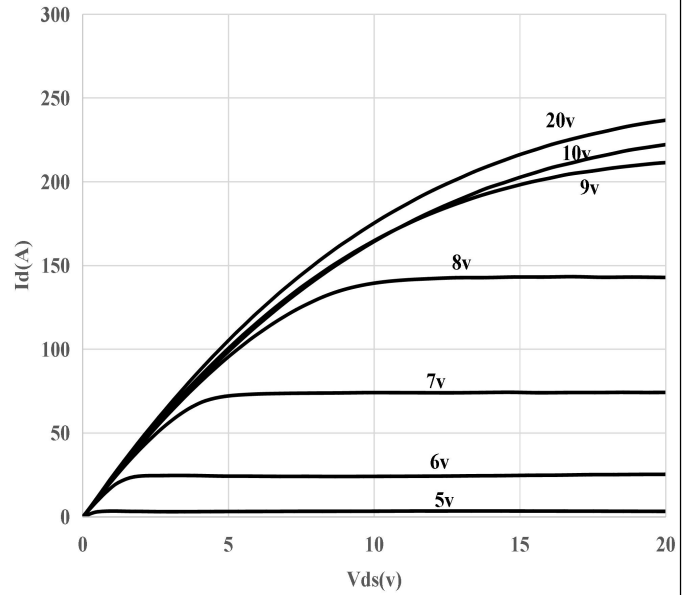
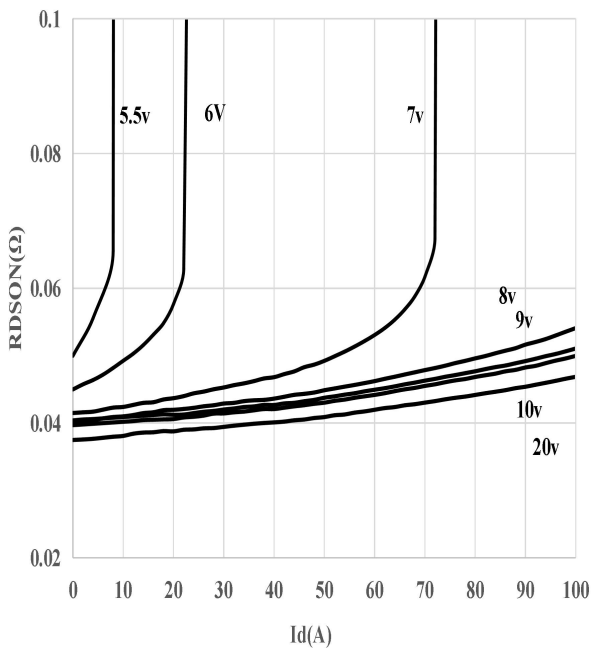
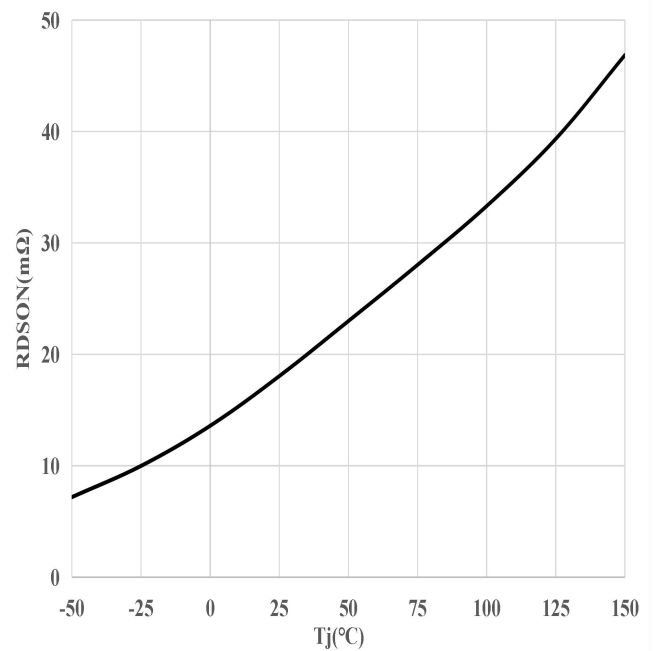
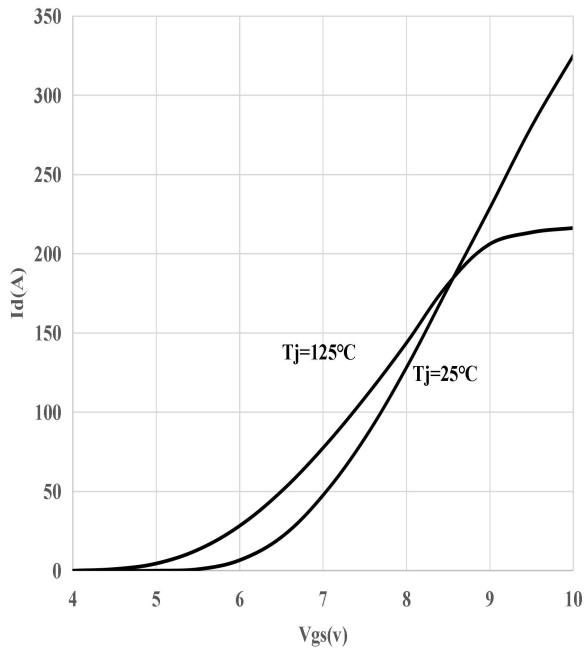
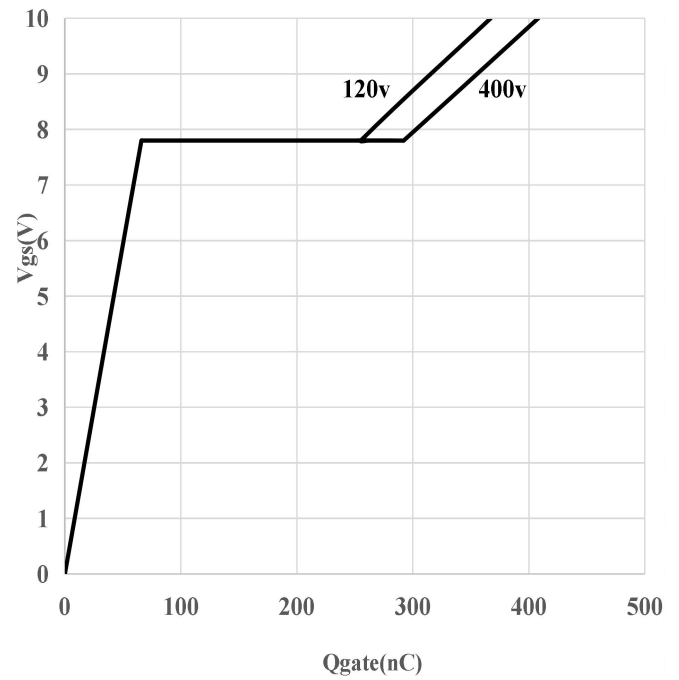
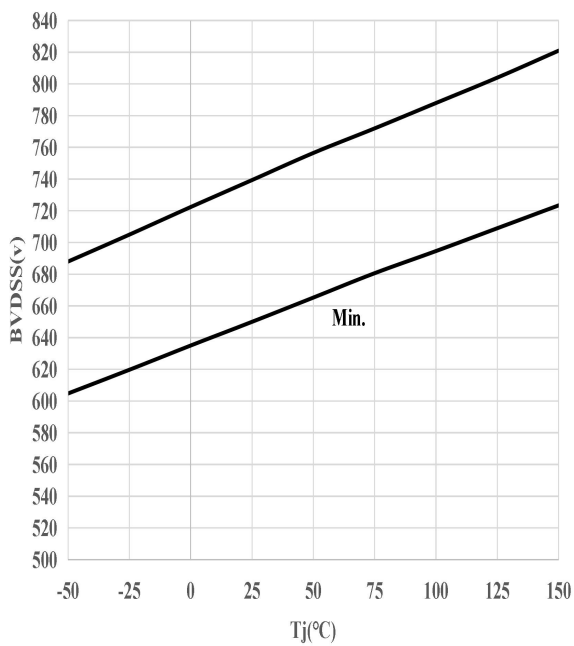
Figure 7: Typ. Output Characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$
Figure 8: Typ. Output Characteristics

 $I_D = f(V_{DS}); T_j = 125^\circ\text{C}; \text{parameter: } V_{GS}$
Figure 9: Typ. Drain-Source On-State Resistance

 $R_{DS(ON)} = f(I_D); T_j = 125^\circ\text{C}; \text{parameter: } V_{GS}$
Figure 10: Typ. Drain-Source On-State Resistance

 $R_{DS(ON)} = f(T_j); I_D = 40\text{A}; V_{GS} = 10\text{V}$

Figure 11: Typ. Transfer Characteristics


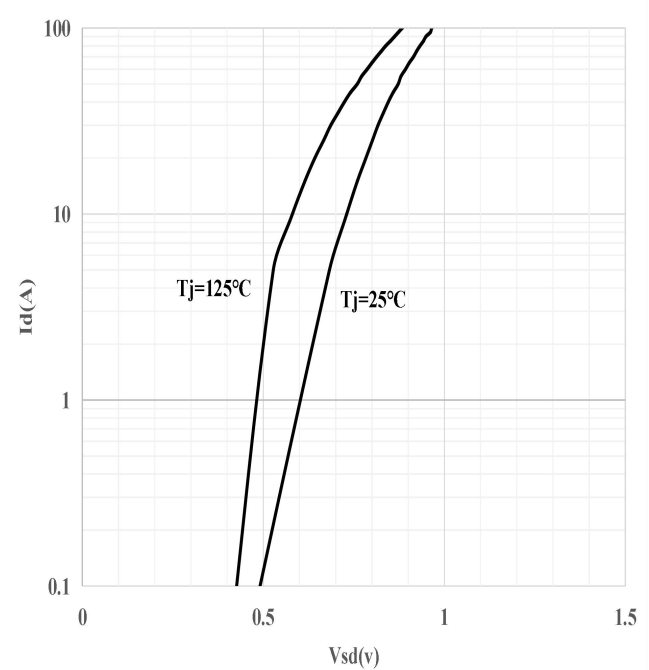
$$I_D = f(V_{GS}); V_{DS} = 20V$$

Figure 12: Typ. Gate Charge


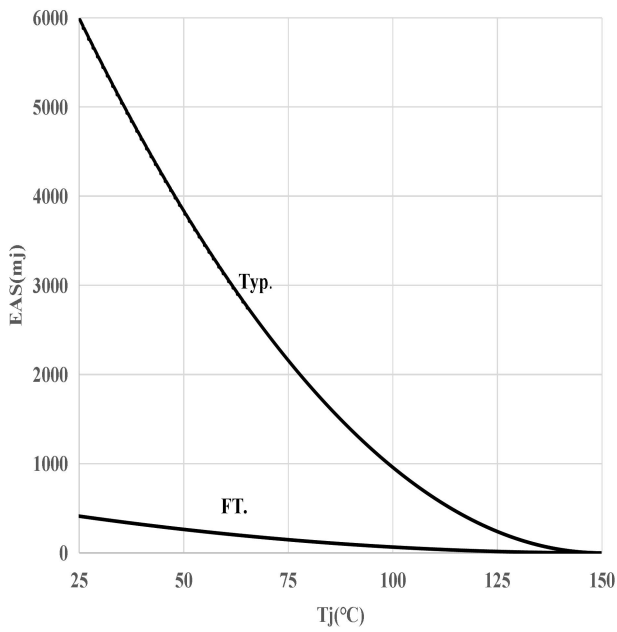
$$V_{GS} = f(Q_{gate}), I_D = 40A \text{ pulsed}$$

Figure 13: Drain-Source Breakdown Voltage


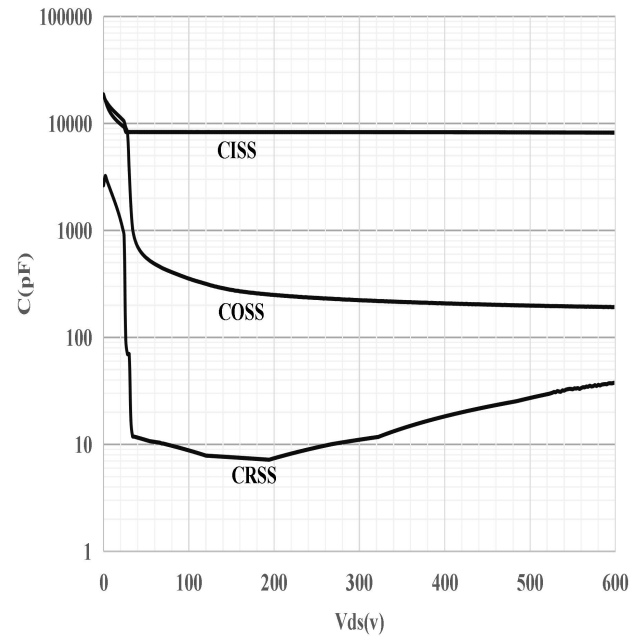
$$V_{BR(DSS)} = f(T_j); I_D = 10mA$$

Figure 14: Forward Characteristics of Reverse Diode


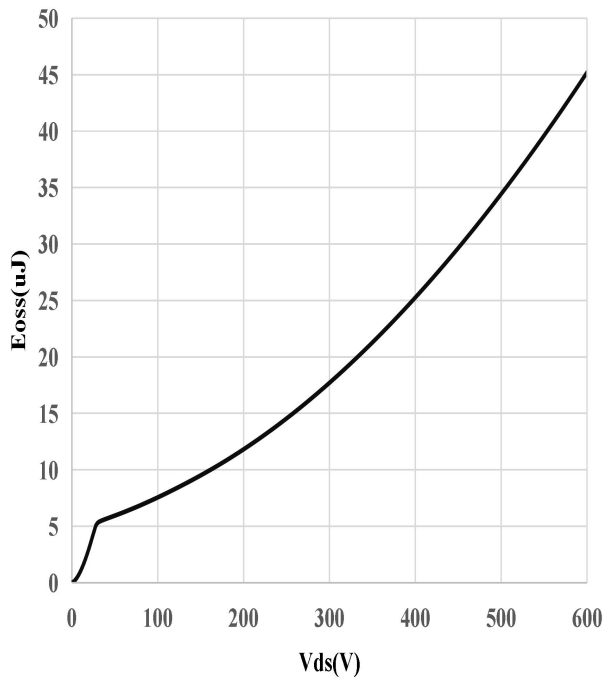
$$I_F = f(V_{SD}); \text{parameter: } T_j$$

24mΩ, 650V, Super Junction N-Channel Power MOSFET
SRC65R024BS
Figure 15: Avalanche Energy


$$E_{AS}=f(T_j); V_{DD}=60V$$

Figure 16: Typ. Capacitances


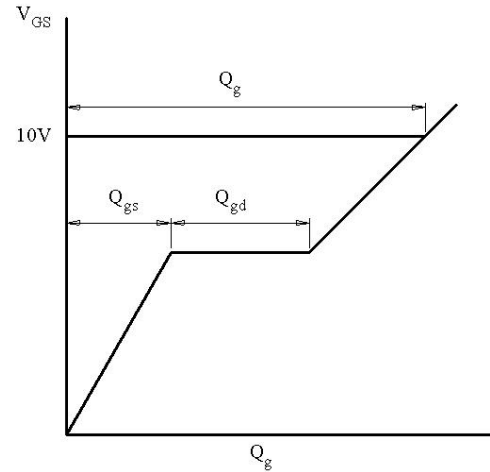
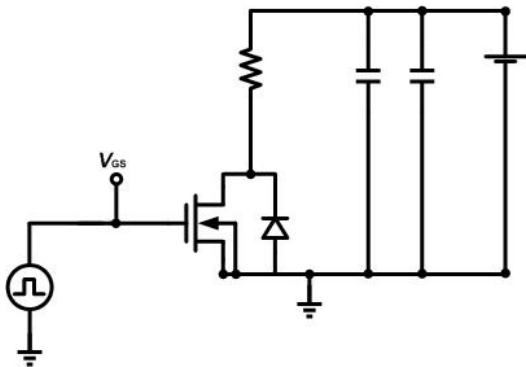
$$C=f(V_{DS}); V_{GS}=0; f=100KHz$$

Figure 17: Coss Stored Energy


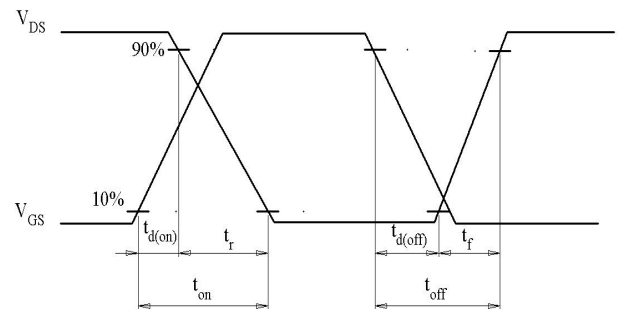
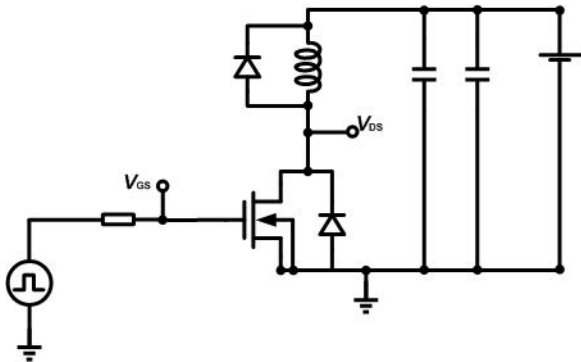
$$E_{OSS}=f(V_{DS})$$

Test Circuits

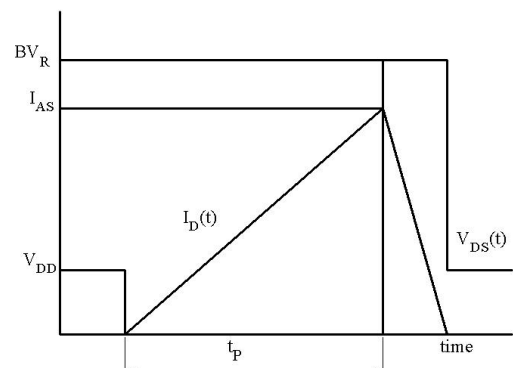
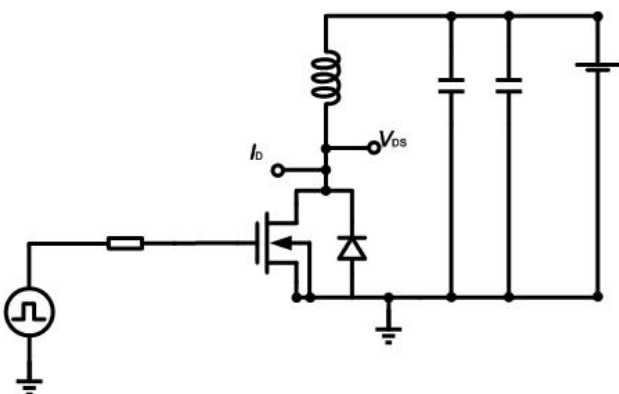
1. Gate Charge Test Circuit & Waveform



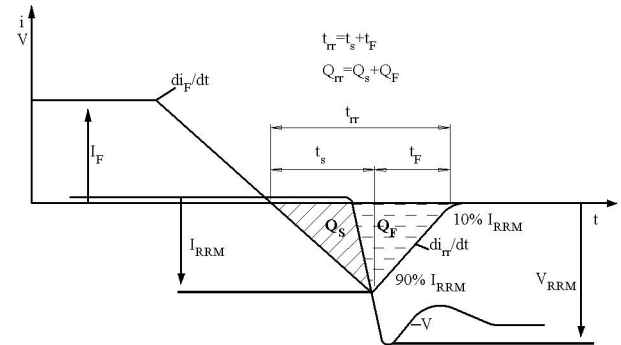
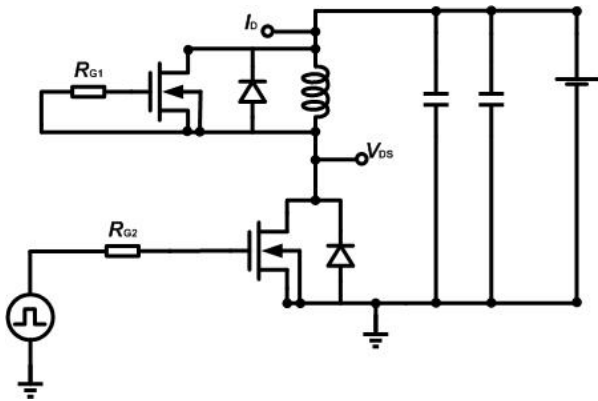
2. Switch Time Test Circuit

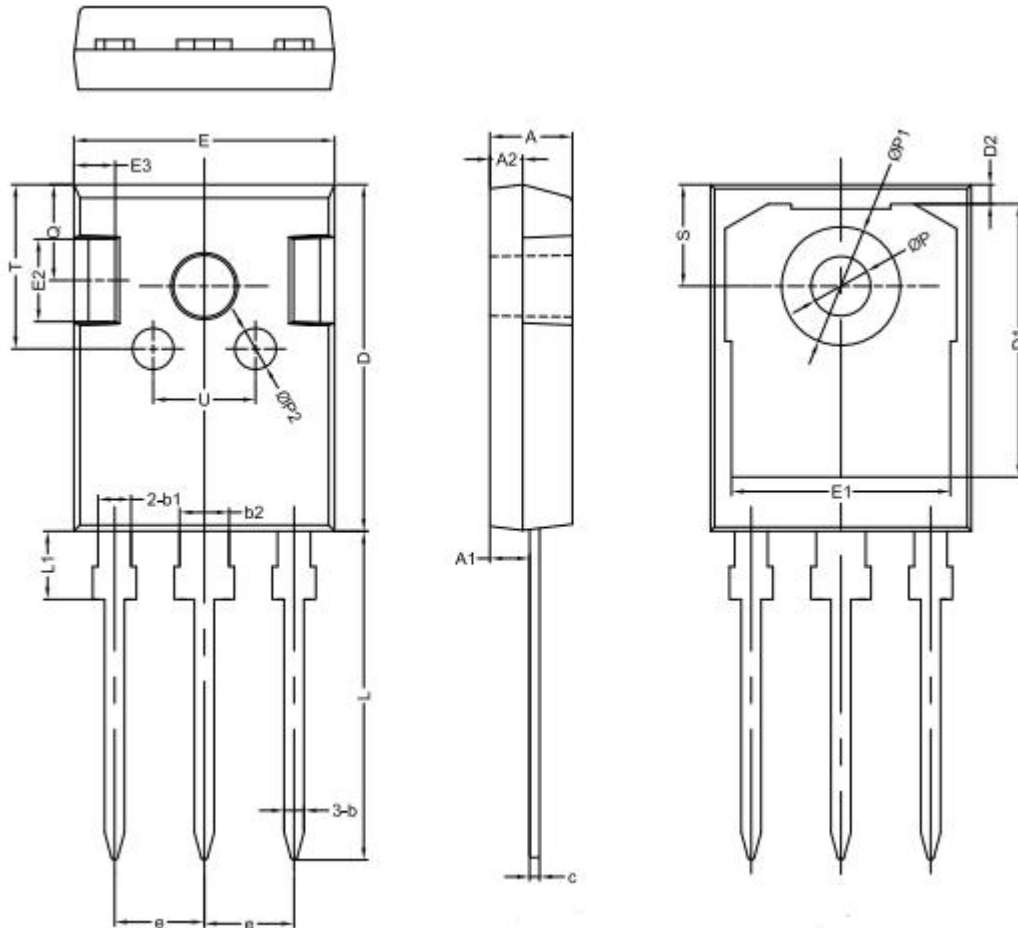


3. Unclaimed Inductive Switching Test Circuit & Waveforms

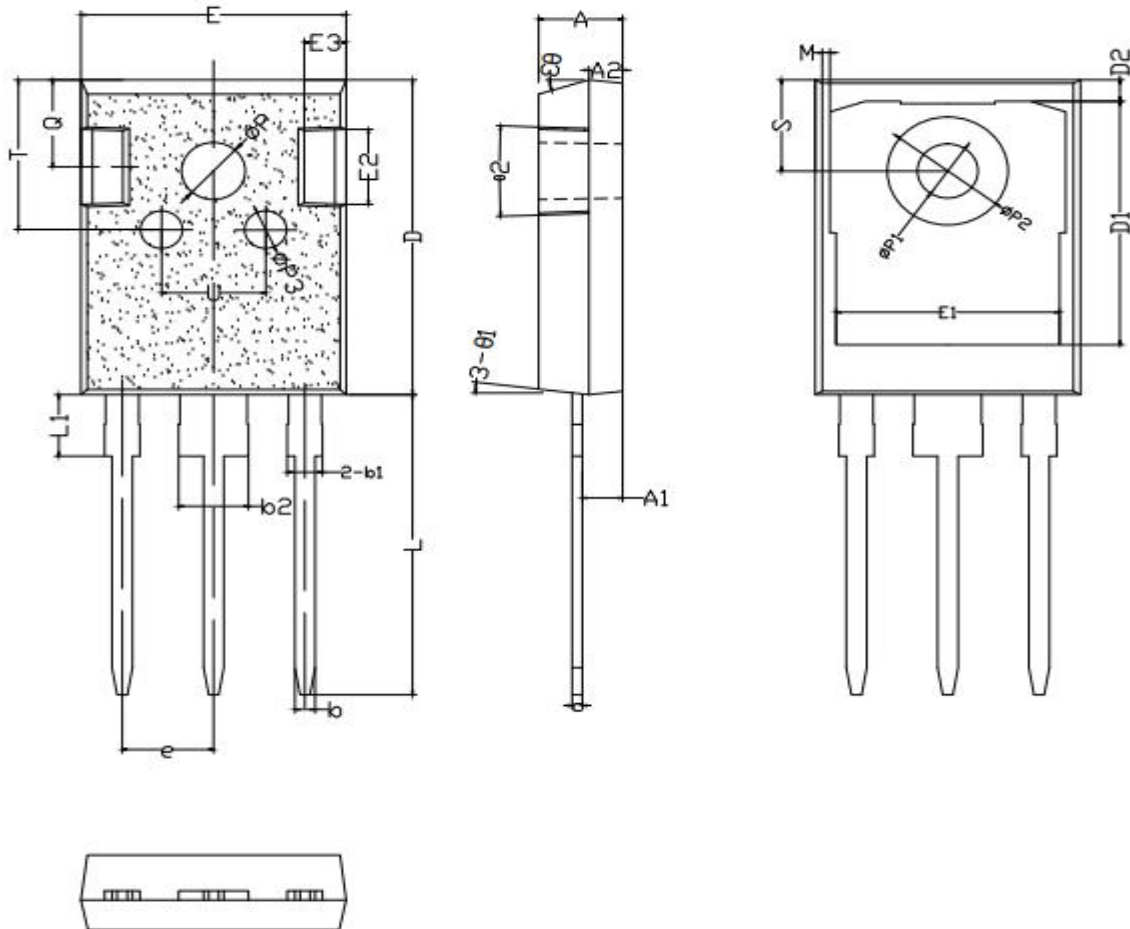


4. Test Circuit and Waveform for Diode Characteristics

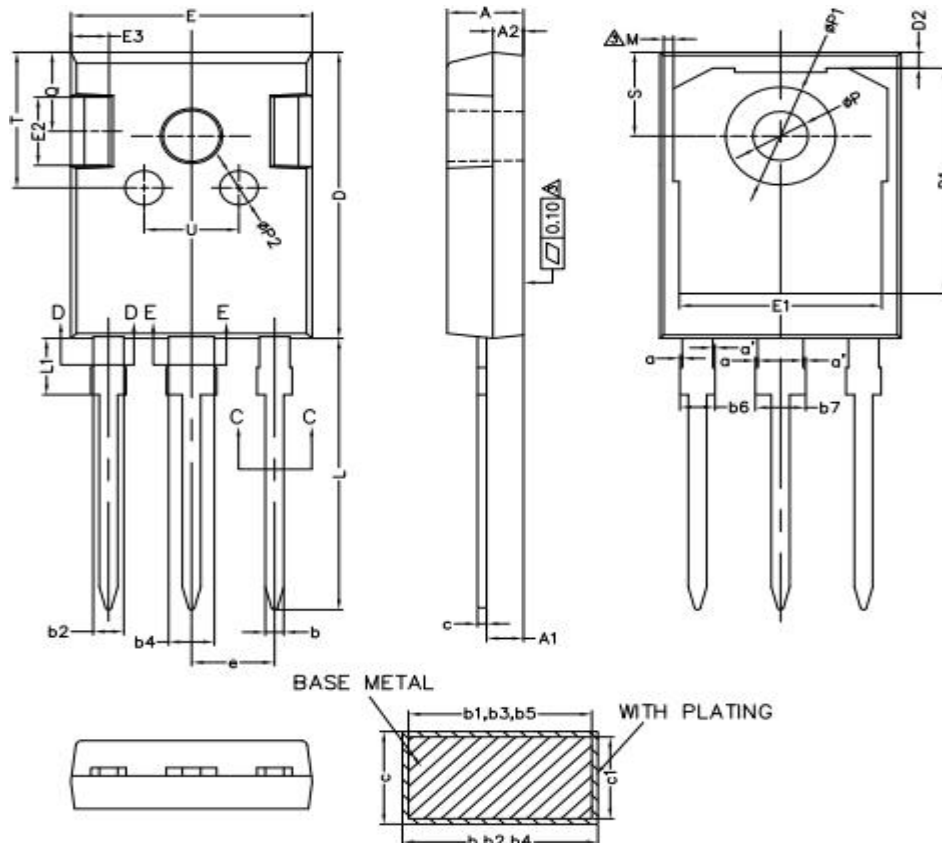


Mechanical Dimensions
TO-247(Package 1)
Unit: mm


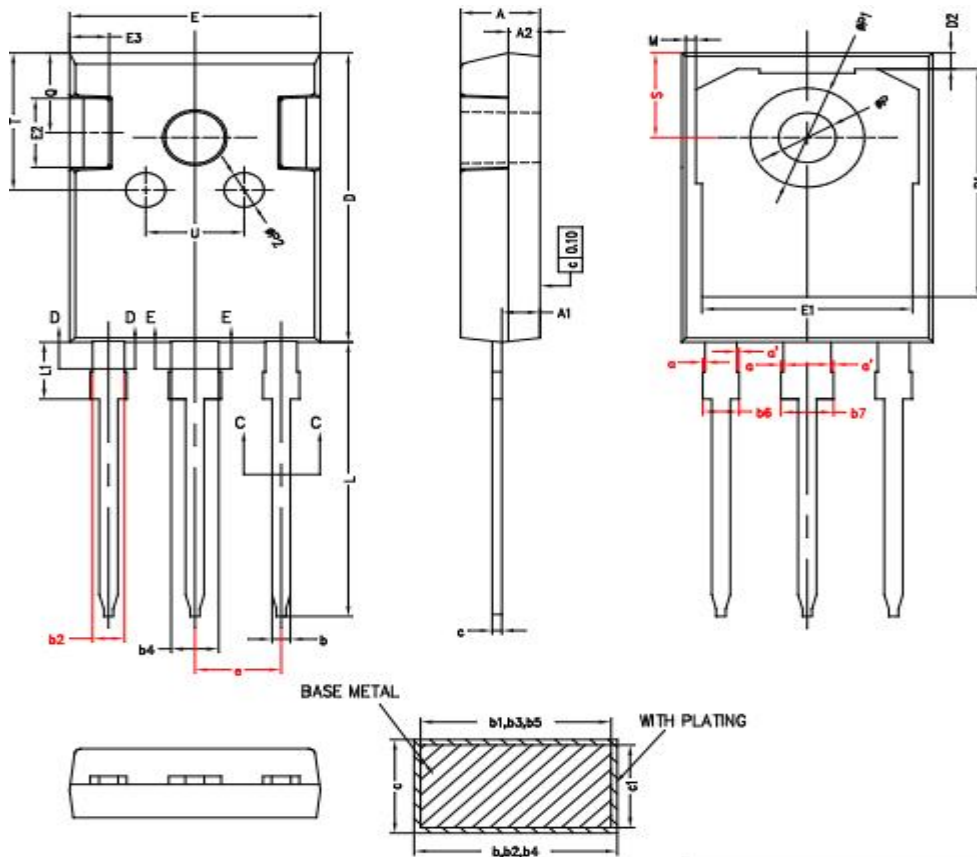
Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.80	5.00	5.20	E1	-	13.30	-
A1	2.21	2.41	2.61	E2	-	5.00	-
A2	1.90	2.00	2.10	E3	-	2.50	-
b	1.10	1.20	1.35	L	19.42	19.92	20.42
b1	-	2.00	-	L1	-	4.13	-
b2	-	3.00	-	P	3.50	3.60	3.70
c	0.55	0.60	0.75	P1	-	7.19	-
D	20.80	21.00	21.20	P2	-	2.50	-
D1	-	16.55	-	Q	-	5.80	-
D2	-	1.20	-	S	6.05	6.15	6.25
E	15.60	15.80	16.0	T	-	10.00	-
U	-	6.20	-				

Mechanical Dimensions
TO-247(Package 2)
Unit: mm


Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.90	5.00	5.10	E1	13.10	13.25	13.40
A1	2.31	2.41	2.51	E2	4.85	4.95	5.10
A2	1.90	2.00	2.10	E3	2.40	2.50	2.60
b	1.15	1.20	1.25	L	19.80	19.98	20.15
b1	1.95	2.10	2.25	L1	-	-	4.30
b2	2.95	3.10	3.25	ΦP	3.60	3.70	3.80
c	0.55	0.60	0.65	ΦP1	3.40	3.50	3.60
D	20.90	21.00	21.10	ΦP2	6.90	7.10	7.30
D1	16.35	16.55	16.75	Q	5.60	5.80	6.00
D2	1.05	1.20	1.35	S	6.05	6.15	6.25
E	15.70	15.80	15.90	T	9.80	10.00	10.20
U	6.00	6.20	6.40	e	5.40	5.44	5.48
Θ1	5°	7°	9°	ΦP3	2.40	2.50	2.60
Θ2	1°	3°	5°	Θ3	13°	15°	17°

Mechanical Dimensions
TO-247(Package 3)
Unit: mm


Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.90	5.00	5.10	c1	0.58	0.60	0.62
A1	2.31	2.41	2.51	D	20.90	21.00	21.10
A2	1.90	2.00	2.10	D1	16.25	16.55	16.85
b	1.16	-	1.26	D2	1.05	1.20	1.35
b1	1.15	1.20	1.22	E	15.70	15.80	15.90
b2	1.96	-	2.06	E1	13.10	13.30	13.50
b3	1.95	2.00	2.02	E2	4.90	5.00	5.10
b4	2.96	-	3.06	E3	2.40	2.50	2.60
b5	2.95	3.00	3.02	e	5.34	5.44	5.54
b6	-	-	2.25	L	19.80	19.92	20.10
b7	-	-	3.25	L1	3.95	4.13	4.30
c	0.59	-	0.66	M	0.35	-	0.95
P	3.50	3.60	3.70	P1	7.00	-	7.40
P2	2.40	2.50	2.60	Q	5.60	-	6.00
S	6.05	6.15	6.25	T	9.80	-	10.20
U	6.00	-	6.40	a	0	-	0.15
a'	0	-	0.15				

Mechanical Dimensions
TO-247(Package 4)
Unit: mm


Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.90	5.00	5.10	E2	4.90	5.00	5.10
A1	2.31	2.41	2.51	E3	2.40	2.50	2.60
A2	1.90	2.00	2.10	e	5.34	5.44	5.54
b	1.12	-	1.22	L	19.80	19.92	20.10
b1	1.11	1.16	1.18	L1	3.95	4.13	4.30
b2	1.96	-	2.06	P	3.50	3.60	3.70
c	0.59	-	0.66	P1	7.00	-	7.40
D	20.90	21.00	21.10	P2	2.40	2.50	2.60
D1	16.25	16.55	16.85	Q	5.60	-	6.00
D2	1.05	1.20	1.35	S	6.05	6.15	6.25
E	15.70	15.80	15.90	T	9.80	-	10.20
E1	13.10	13.30	13.50	U	6.00	-	6.40
b3	1.95	2.00	2.02	b6	-	-	2.25
b4	2.96	-	3.06	b7	-	-	3.25
b5	2.95	3.00	3.02	c1	0.58	0.60	0.62
M	0.35	-	0.95	a	0	-	0.15
a'	0	-	0.15				



Shenzhen Sanrise Technology Co., LTD

<http://www.sanrise-tech.com>

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